

Abstract Submitted
for the MAR15 Meeting of
The American Physical Society

Giant thermal spin torque assisted magnetic tunnel junction switching AAKASH PUSHP, TIMOTHY PHUNG, CHARLES RETTNER, BRIAN HUGHES, SEE-HUN YANG, STUART PARKIN, IBM Almaden Research Center — Spin-polarized charge-currents induce magnetic tunnel junction (MTJ) switching by virtue of spin-transfer-torque (STT). Recently, by taking advantage of the spin-dependent thermoelectric properties of magnetic materials, novel means of generating spin-currents from temperature gradients, and their associated thermal-spin-torques (TSTs) have been proposed, but so far these TSTs have not been large enough to influence MTJ switching. Here we demonstrate significant TSTs in MTJs by generating large temperature gradients across ultrathin MgO tunnel barriers that considerably affect the switching fields of the MTJ. We attribute the origin of the TST to an asymmetry of the tunneling conductance across the zero-bias voltage of the MTJ. Remarkably, we estimate through magneto-Seebeck voltage measurements that the charge-currents that would be generated due to the temperature gradient would give rise to STT that is a thousand times too small to account for the changes in switching fields that we observe.

Aakash Pushp
IBM Almaden Research Center

Date submitted: 14 Nov 2014

Electronic form version 1.4